

**P-CHANNEL MOS FIELD EFFECT TRANSISTOR
FOR SWITCHING**

DESCRIPTION

The μ PA1817 is a switching device which can be driven directly by a 2.5 V power source.

This device features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power management of notebook computers and so on.

FEATURES

- 2.5 V drive available
- Low on-state resistance
 $R_{DS(on)1} = 12 \text{ m}\Omega \text{ MAX. (} V_{GS} = -4.5 \text{ V, } I_D = -6.0 \text{ A)}$
 $R_{DS(on)2} = 12.5 \text{ m}\Omega \text{ MAX. (} V_{GS} = -4.0 \text{ V, } I_D = -6.0 \text{ A)}$
 $R_{DS(on)3} = 19.2 \text{ m}\Omega \text{ MAX. (} V_{GS} = -2.5 \text{ V, } I_D = -6.0 \text{ A)}$
- Built-in G-S protection diode against ESD

ORDERING INFORMATION

PART NUMBER	PACKAGE
μ PA1817GR-9JG	Power TSSOP8

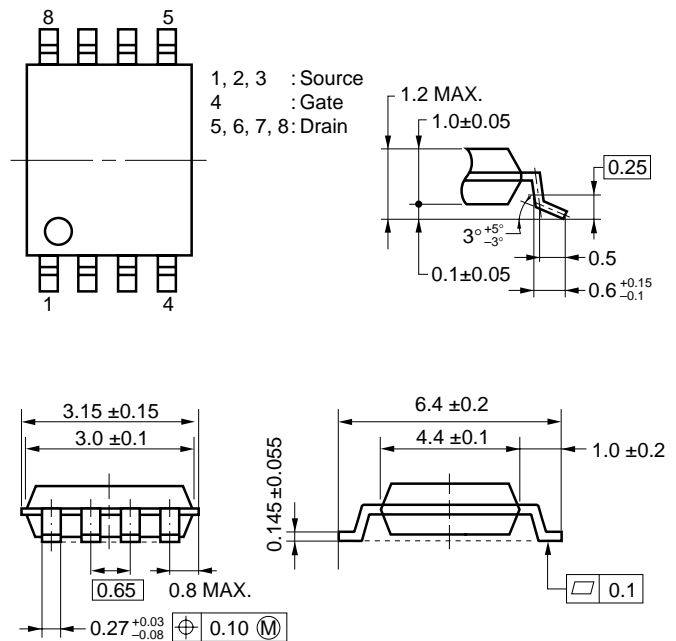
ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

Drain to Source Voltage (V _{GS} = 0 V)	V _{DSS}	-20	V
Gate to Source Voltage (V _{DS} = 0 V)	V _{GSS}	∓ 12	V
Drain Current (DC) (T _A = 25°C)	I _{D(DC)}	∓ 12	A
Drain Current (pulse) ^{Note1}	I _{D(pulse)}	∓ 48	A
Total Power Dissipation ^{Note2}	P _T	2.0	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

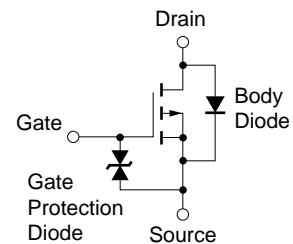
- Notes 1.** PW ≤ 10 μs, Duty Cycle ≤ 1%
2. Mounted on ceramic substrate of 5000 mm² x 1.1 mm

Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

PACKAGE DRAWING (Unit: mm)



EQUIVALENT CIRCUIT

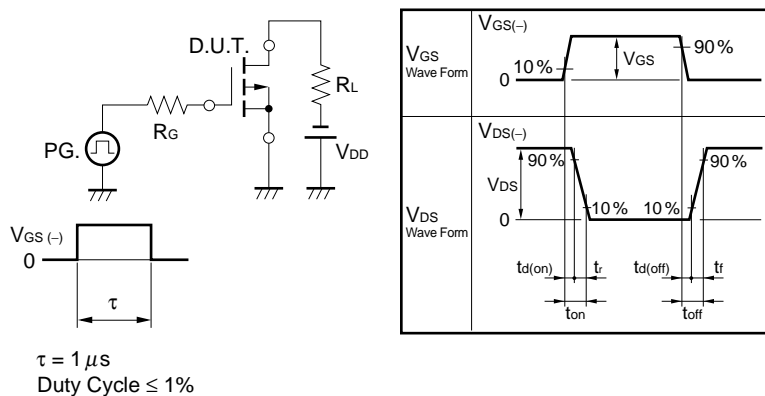


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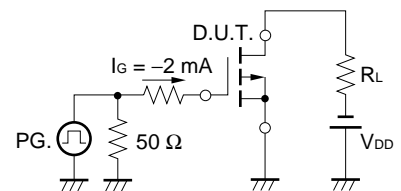
ELECTRICAL CHARACTERISTICS (T_A = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -20 V, V _{GS} = 0 V			-1.0	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±12 V, V _{DS} = 0 V			±10	μA
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = -10 V, I _D = -1.0 mA	-0.5	-1.1	-1.5	V
Forward Transfer Admittance	y _{fs}	V _{DS} = -10 V, I _D = -6.0 A	15	30		S
Drain to Source On-state Resistance	R _{DS(on)1}	V _{GS} = -4.5 V, I _D = -6.0 A		9.6	12	mΩ
	R _{DS(on)2}	V _{GS} = -4.0 V, I _D = -6.0 A		10	12.5	mΩ
	R _{DS(on)3}	V _{GS} = -2.5 V, I _D = -6.0 A		14.5	19.2	mΩ
Input Capacitance	C _{iss}	V _{DS} = -10 V		3100		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V		730		pF
Reverse Transfer Capacitance	C _{rss}	f = 1.0 MHz		450		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = -10 V, I _D = -6.0 A		29		ns
Rise Time	t _r	V _{GS} = -4.0 V		235		ns
Turn-off Delay Time	t _{d(off)}	R _G = 10 Ω		170		ns
Fall Time	t _f			230		ns
Total Gate Charge	Q _G	V _{DD} = -16 V		27		nC
Gate to Source Charge	Q _{GS}	V _{GS} = -4.0 V		5.6		nC
Gate to Drain Charge	Q _{GD}	I _D = -12 A		12		nC
Body Diode Forward Voltage	V _{F(S-D)}	I _F = 12 A, V _{GS} = 0 V		0.82		V
Reverse Recovery Time	t _{rr}	I _F = 12 A, V _{GS} = 0 V		70		ns
Reverse Recovery Charge	Q _{rr}	di/dt = 100 A/μs		52		nC

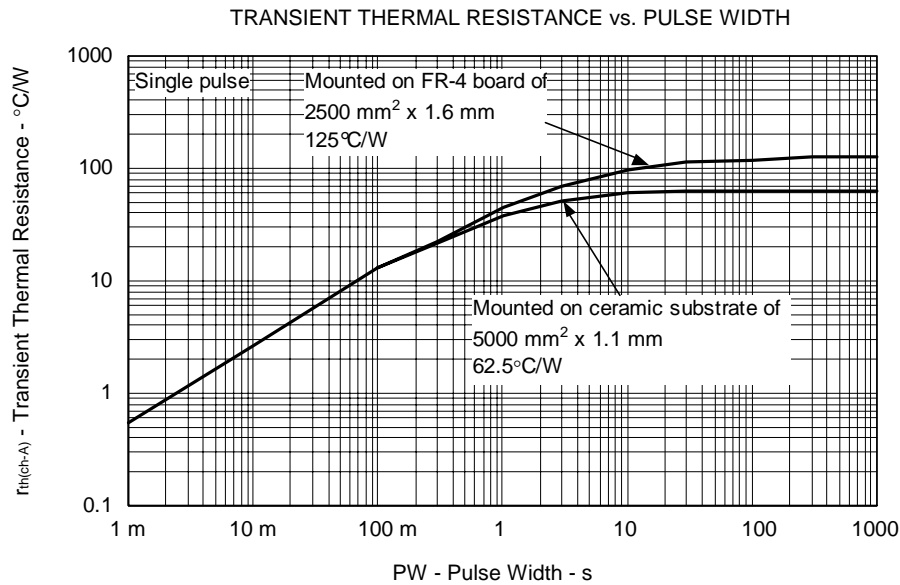
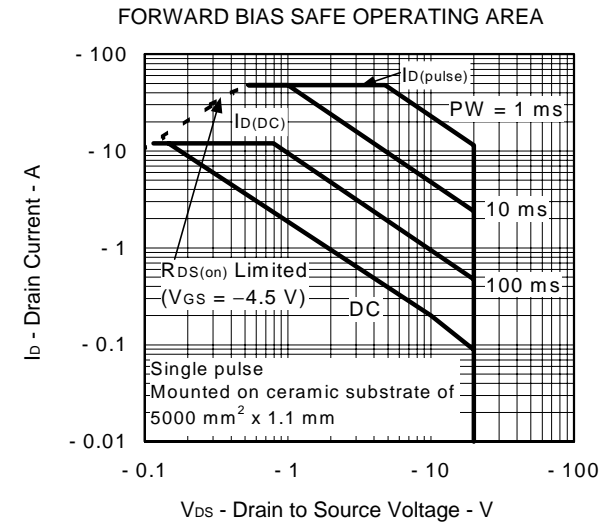
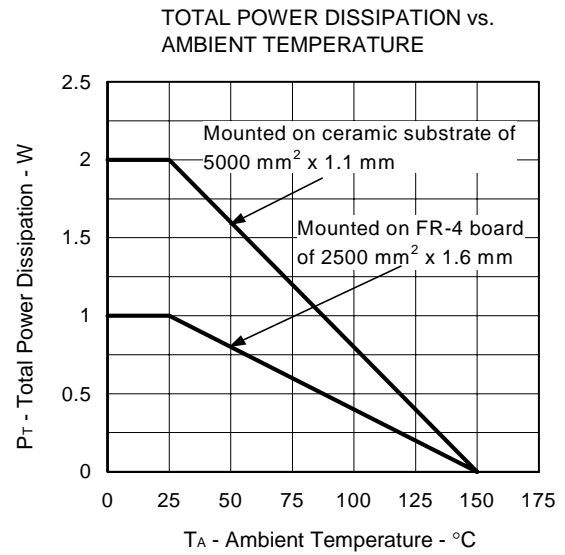
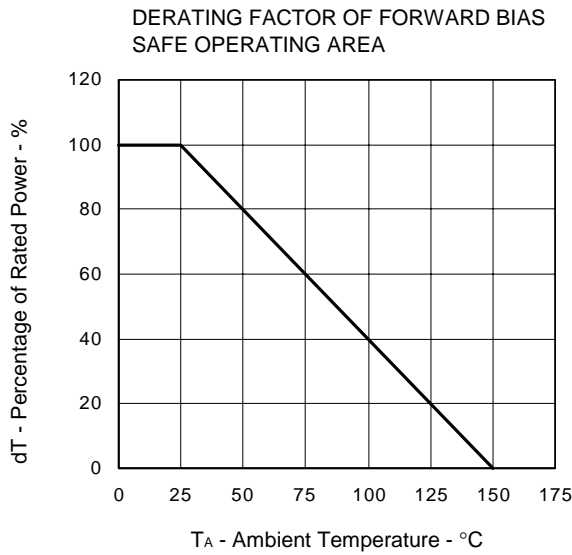
TEST CIRCUIT 1 SWITCHING TIME



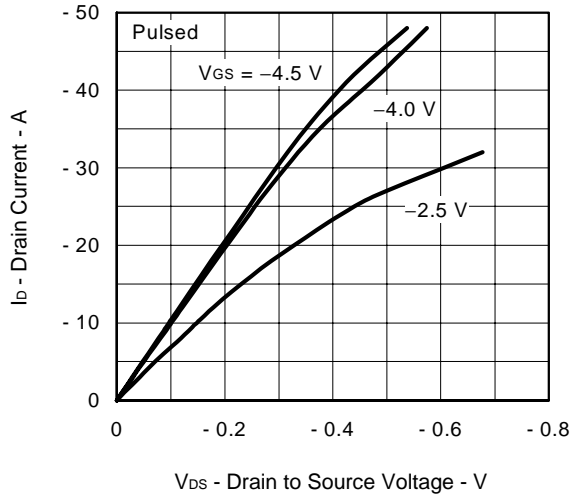
TEST CIRCUIT 2 GATE CHARGE



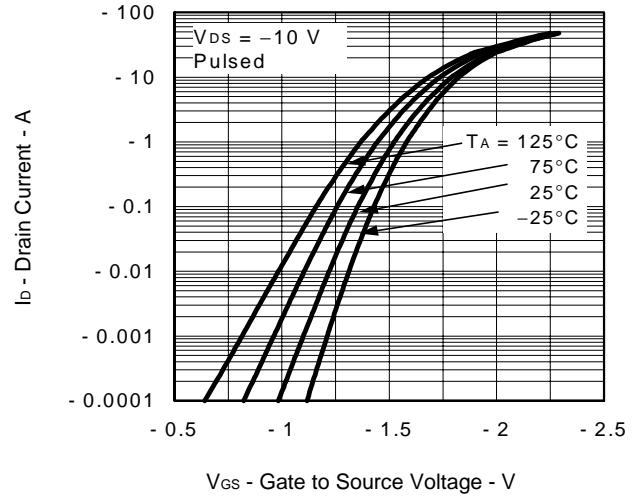
TYPICAL CHARACTERISTICS (T_A = 25°C)



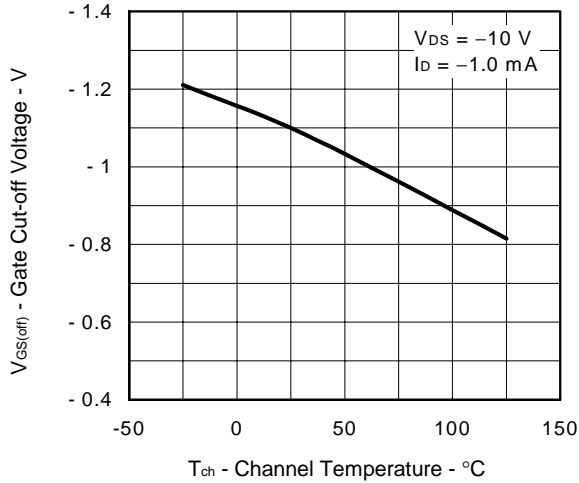
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



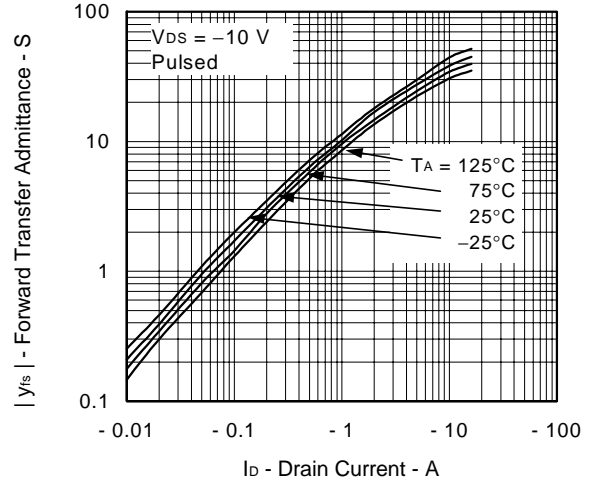
FORWARD TRANSFER CHARACTERISTICS



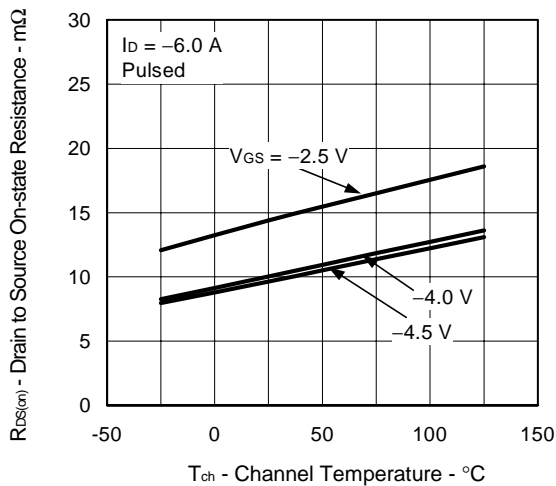
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



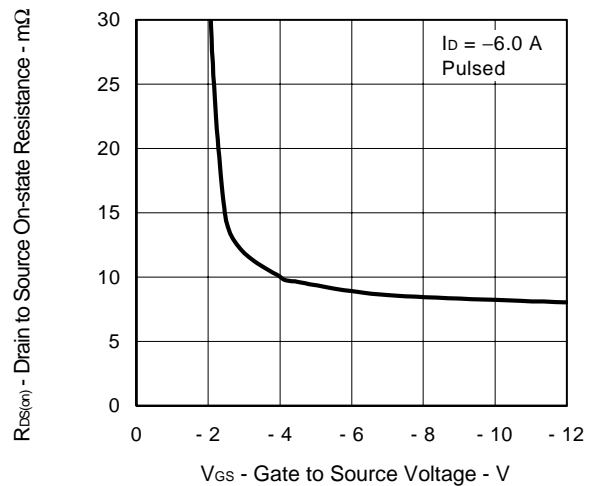
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



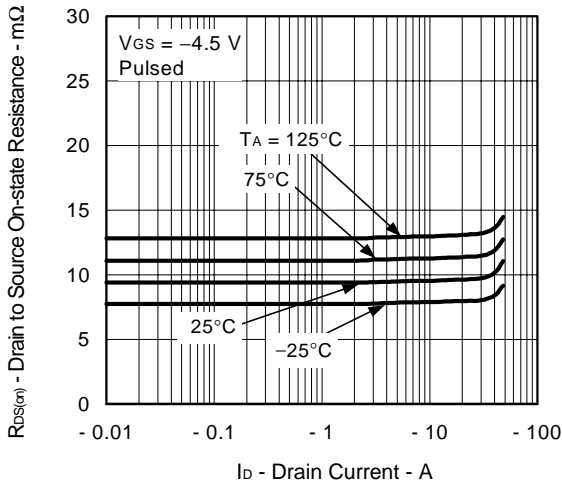
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



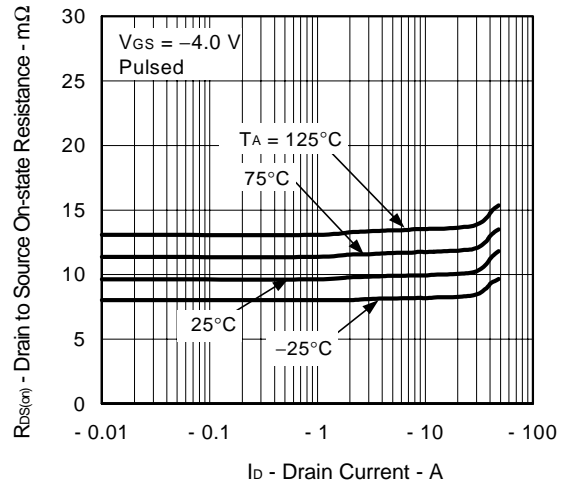
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



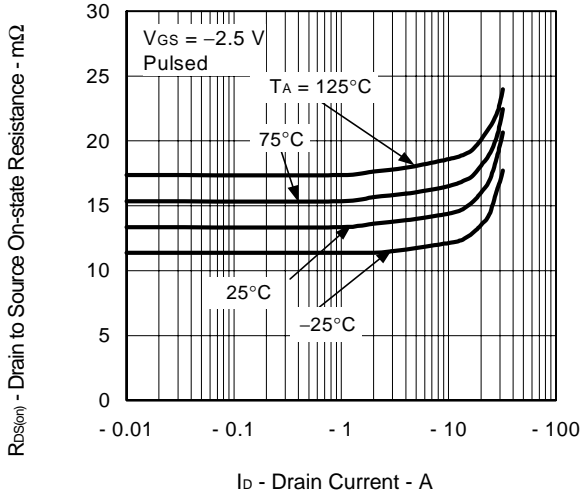
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



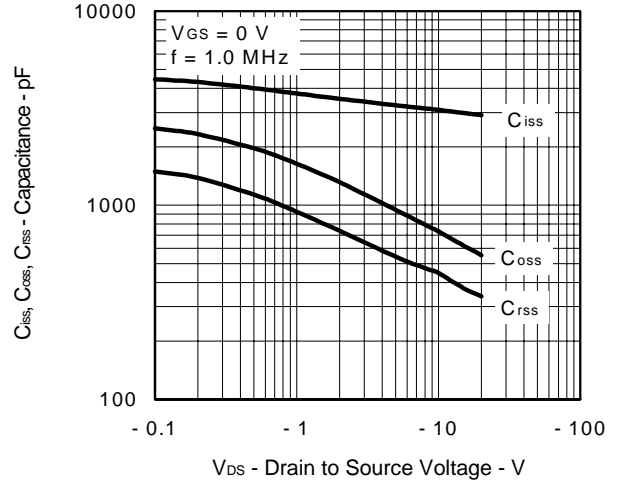
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



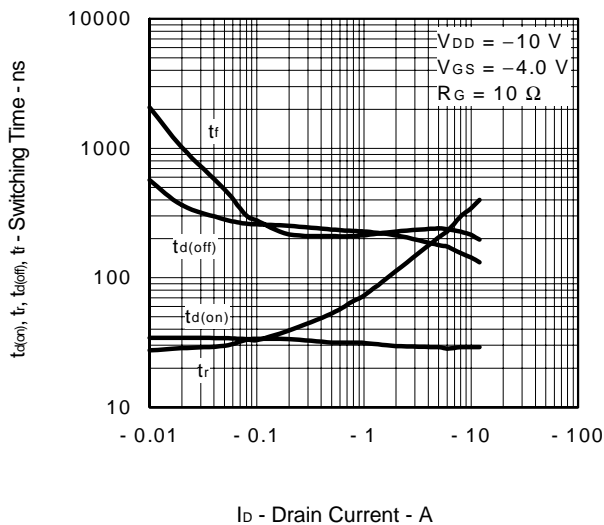
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



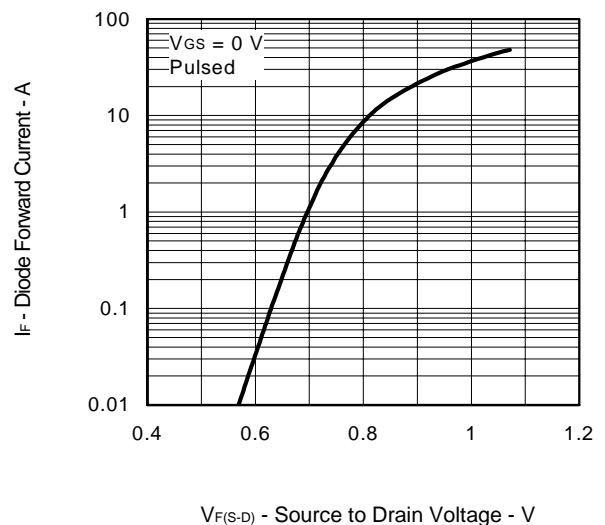
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



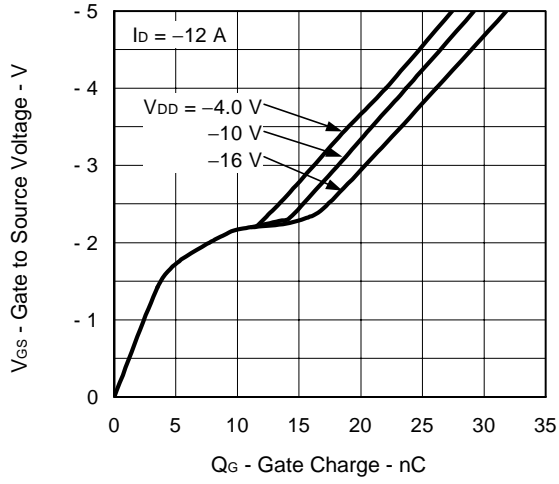
SWITCHING CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



DYNAMIC INPUT/OUTPUT CHARACTERISTICS



[MEMO]

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